

TECHNICAL SPECIFICATION		
Features	Units	Available planes
		C-plane (0001)
Carrier concentration	cm <sup>-3</sup>	~10 <sup>19</sup>
Dopant		Oxygen
Resistivity	Ωcm	~10 <sup>-3</sup>
Mobility	cm <sup>2</sup> /Vs	~150
Thickness	μm	300-400 ±50
TTV	μm	≤40
Bow	μm	≤10
FWHM (0002) of XRC, (epi-ready; 0.1x0.1 mm slit)	arcsec	~20
Etch Pits Density (EPD)	cm <sup>-2</sup>	~5x10 <sup>4</sup>
Off-cut	deg	0.3±0.1 to the m-direction
Surface finishing	Front side	epi-ready (RMS < 0.5 nm)
	Back side	rough
Available sizes		10x10mm
		1-inch
		1.5-inch
Packaging		separate single wafer container
Special request		for pricing or technical enquiries please contact our sales team

Round shape

